



12/23/96

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1-18MPATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of)
 Ritu Shrivastava, et al.)
 Serial No.: 08/456,080)
 Filed: May 29, 1996)
 For: DRAM CELL WITH SELF-)
 ALIGNED CONTACT AND)
 METHOD OF)
 FABRICATING SAME)

Group Art Unit: 1107

Examiner: H. Tsai

RECEIVED

JAN 10 1997

GROUP 1100

RESPONSE TO OFFICE ACTION

MAILED SEPTEMBER 20, 1996

Honorable Commissioner of Patents
 and Trademarks
 Washington, D.C. 20231

CERTIFICATE OF MAILING	
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks.	
Washington, DC 20231 on	12/20/96
	LIMBACH & LIMBACH (LLP)
Dated: 12/20/96	By: J. M. Lattig
	Name

Sir:

Please amend the above-identified application as follows:

IN THE TITLE:

Please delete the title in its entirety and substitute the following new title:

-- METHOD OF FABRICATING DRAM CELL WITH
 SELF-ALIGNED CONTACT --

IN THE CLAIMS:

Please amend Claim 6 to read as follows:

1. [Amended] A method of fabricating a dynamic random access memory (DRAM) structure [(100)] in a semiconductor substrate having a first conductivity type, the DRAM structure [(100)] including source [(120)] and drain regions of a second conductivity type that is opposite to the first conductivity type formed in the semiconductor substrate in spaced-apart relationship to define a

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